

Notice of References Cited

Application N .

Applicant(s)

10-076129

He et al

Examiner

George Gaudreau

Group Art Unit

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U.S. PATENT DOCUMENTS

*	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS
A	6436812	8-20-02'	Lee	438	636
B	2002/0132488	9-19-02'	Nollan	438	720
C					
D					
E					
F					
G					
H					
I					
J					
K					
L					
M					

FOREIGN PATENT DOCUMENTS

*	DOCUMENT NO.	DATE	COUNTRY	NAME	CLASS	SUBCLASS
N	61-171,127	8-1-86'	Japan	Yoshichika et al		
O						
P						
Q						
R						
S						
T						

NON-PATENT DOCUMENTS

*	DOCUMENT (Including Author, Title, Source, and Pertinent Pages)	DATE
U	"Implementation of Tungsten Metallization In Multilayer Interconnection Technologies";	
*	IEEE Trans, On Semiconductor Mfg; vol. 3, no. 4; (11-1990'); Riley et al; pp. 156-157	
W	"X-Ray Mask Fabrication Technology For 0.1um Very Large Scale Integrated Circuits"; J. Vac. Sci.;	
*	B; 14(6); (12-1996'); Oda et. al; pp. 4366-4370	

* A copy of this reference is not being furnished with this Office action.
(See Manual of Patent Examining Procedure, Section 707.05(a).)